

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H110C-CDMA BC0-RC3 SO55-777CH

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 848.31 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 91.11 V/m; Power Drift = -0.03 dB

PMF = 1.050 is applied.

E-field emissions = 75.06 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

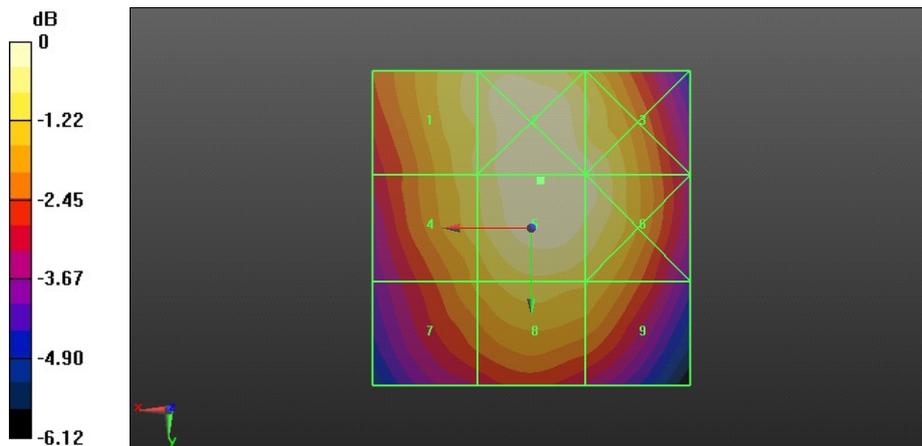
Grid 1 M4 70.34 V/m	Grid 2 M4 75.06 V/m	Grid 3 M4 72.77 V/m
Grid 4 M4 68.81 V/m	Grid 5 M4 75.06 V/m	Grid 6 M4 73.17 V/m
Grid 7 M4 63.04 V/m	Grid 8 M4 67.62 V/m	Grid 9 M4 65.68 V/m

Cursor:

Total = 75.06 V/m

E Category: M4

Location: -1.5, -7.5, 8.7 mm



0 dB = 75.06 V/m = 37.51 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H110C-CDMA BC0-RC3 SO55-384CH

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 836.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 99.87 V/m; Power Drift = 0.03 dB

PMF = 1.050 is applied.

E-field emissions = 81.97 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

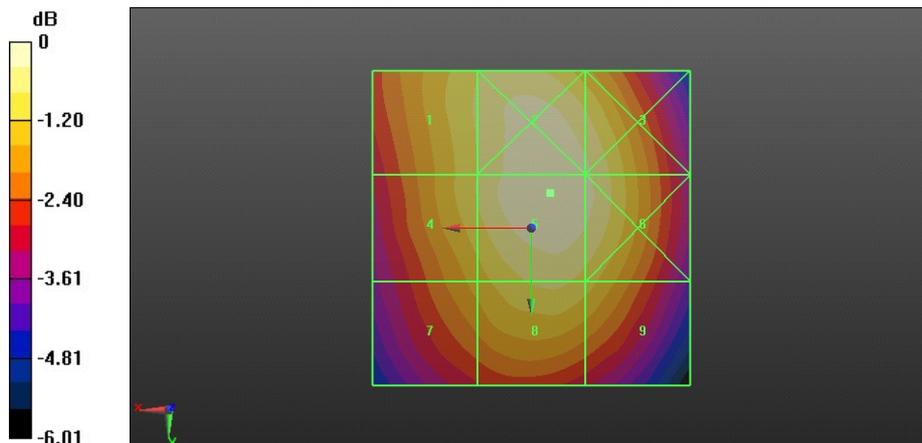
Grid 1 M4 75.34 V/m	Grid 2 M4 81.41 V/m	Grid 3 M4 79.10 V/m
Grid 4 M4 75.03 V/m	Grid 5 M4 81.97 V/m	Grid 6 M4 79.54 V/m
Grid 7 M4 69.63 V/m	Grid 8 M4 75.56 V/m	Grid 9 M4 73.10 V/m

Cursor:

Total = 81.97 V/m

E Category: M4

Location: -3, -5.5, 8.7 mm



0 dB = 81.97 V/m = 38.27 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H110C-CDMA BC0-RC3 SO55-1013CH

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 824.7 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 98.54 V/m; Power Drift = 0.02 dB

PMF = 1.050 is applied.

E-field emissions = 80.41 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

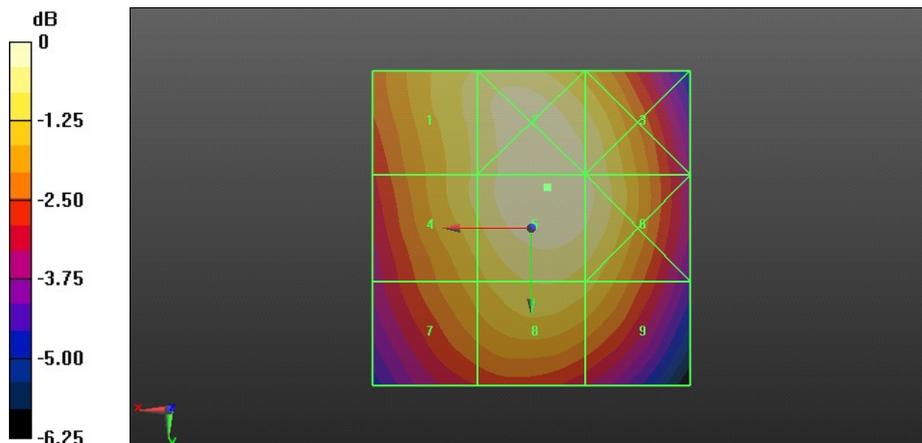
Grid 1 M4 74.82 V/m	Grid 2 M4 80.29 V/m	Grid 3 M4 77.29 V/m
Grid 4 M4 74.32 V/m	Grid 5 M4 80.41 V/m	Grid 6 M4 77.93 V/m
Grid 7 M4 68.45 V/m	Grid 8 M4 73.35 V/m	Grid 9 M4 71.14 V/m

Cursor:

Total = 80.41 V/m

E Category: M4

Location: -2.5, -6.5, 8.7 mm



0 dB = 80.41 V/m = 38.11 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H110C-CDMA BC0-RC3 SO55-384CH with battery 2#

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 836.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 98.12 V/m; Power Drift = -0.08 dB

PMF = 1.050 is applied.

E-field emissions = 79.05 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

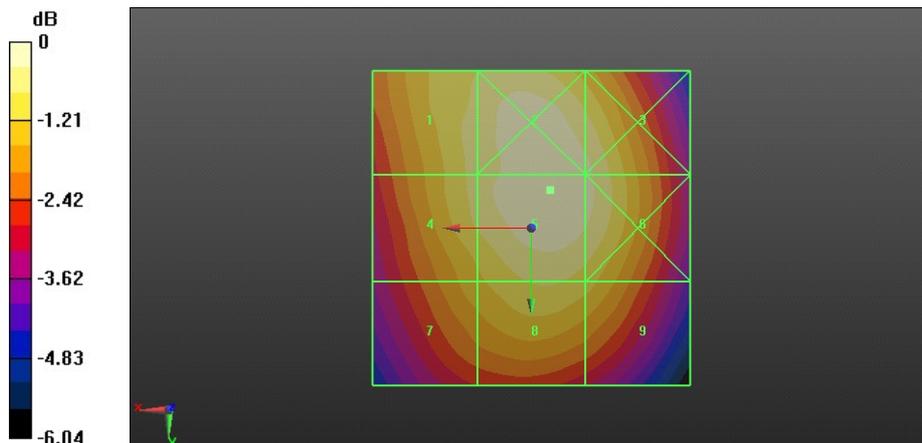
Grid 1 M4 73.82 V/m	Grid 2 M4 78.82 V/m	Grid 3 M4 76.50 V/m
Grid 4 M4 73.47 V/m	Grid 5 M4 79.05 V/m	Grid 6 M4 76.74 V/m
Grid 7 M4 68.02 V/m	Grid 8 M4 72.45 V/m	Grid 9 M4 70.28 V/m

Cursor:

Total = 79.05 V/m

E Category: M4

Location: -3, -6, 8.7 mm



0 dB = 79.05 V/m = 37.96 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H110C-CDMA BC1-RC3 SO55-1175CH

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1908.75 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 51.52 V/m; Power Drift = -0.08 dB

PMF = 1.020 is applied.

E-field emissions = 45.56 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

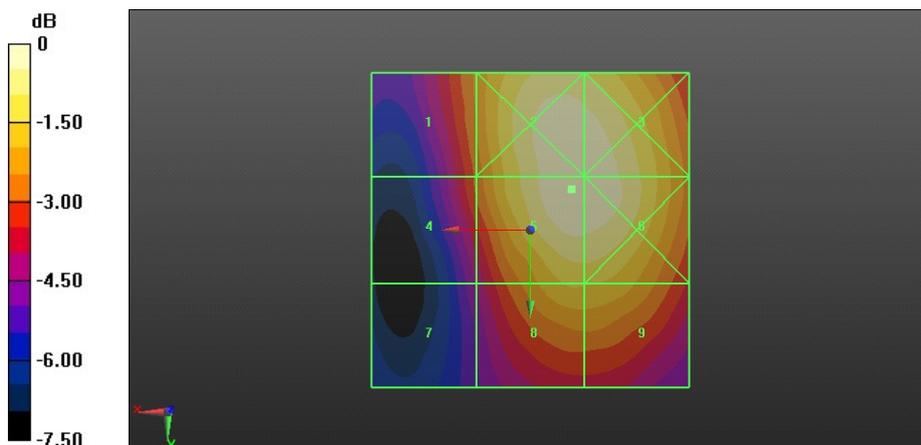
Grid 1 M4 34.66 V/m	Grid 2 M4 45.41 V/m	Grid 3 M4 45.22 V/m
Grid 4 M4 32.87 V/m	Grid 5 M4 45.56 V/m	Grid 6 M4 45.35 V/m
Grid 7 M4 27.39 V/m	Grid 8 M4 38.67 V/m	Grid 9 M4 38.57 V/m

Cursor:

Total = 45.56 V/m

E Category: M4

Location: -6.5, -6.5, 8.7 mm



0 dB = 45.56 V/m = 33.17 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H110C-CDMA BC1-RC3 SO55-600CH

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 48.49 V/m; Power Drift = -0.05 dB

PMF = 1.020 is applied.

E-field emissions = 45.73 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

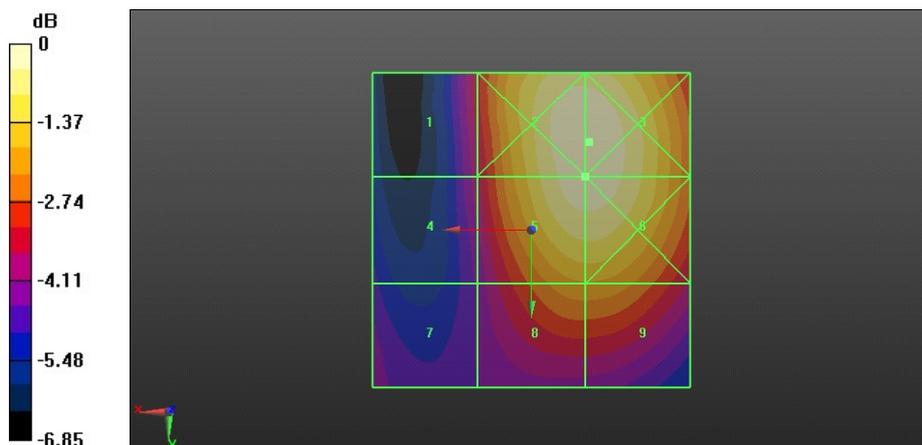
Grid 1 M4 31.57 V/m	Grid 2 M4 46.39 V/m	Grid 3 M4 46.39 V/m
Grid 4 M4 30.01 V/m	Grid 5 M4 45.73 V/m	Grid 6 M4 45.76 V/m
Grid 7 M4 28.60 V/m	Grid 8 M4 37.40 V/m	Grid 9 M4 37.40 V/m

Cursor:

Total = 46.39 V/m

E Category: M4

Location: -9, -14, 8.7 mm



0 dB = 46.39 V/m = 33.33 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H110C-CDMA BC1-RC3 SO55-25CH

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1851.25 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 58.73 V/m; Power Drift = -0.04 dB

PMF = 1.020 is applied.

E-field emissions = 55.42 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

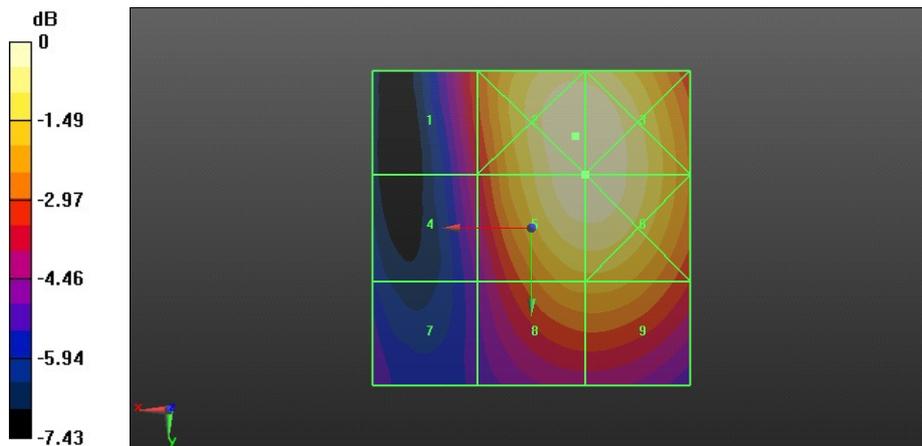
Grid 1 M4 39.63 V/m	Grid 2 M4 55.81 V/m	Grid 3 M4 55.76 V/m
Grid 4 M4 36.25 V/m	Grid 5 M4 55.42 V/m	Grid 6 M4 55.42 V/m
Grid 7 M4 31.85 V/m	Grid 8 M4 45.88 V/m	Grid 9 M4 45.92 V/m

Cursor:

Total = 55.81 V/m

E Category: M4

Location: -7, -14.5, 8.7 mm



0 dB = 55.81 V/m = 34.93 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H110C-CDMA BC1-RC3 SO55-25CH with battery 2#

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1851.25 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 58.90 V/m; Power Drift = 0.02 dB

PMF = 1.020 is applied.

E-field emissions = 55.44 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

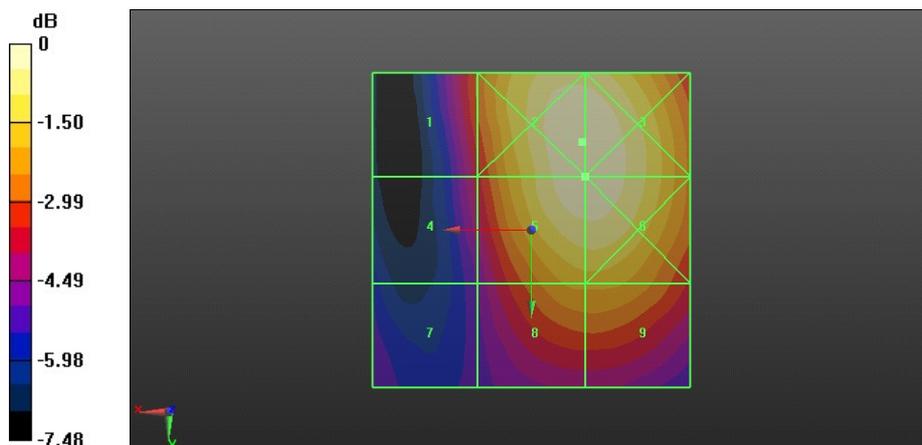
Grid 1 M4 40.38 V/m	Grid 2 M4 56.08 V/m	Grid 3 M4 56.07 V/m
Grid 4 M4 36.64 V/m	Grid 5 M4 55.44 V/m	Grid 6 M4 55.44 V/m
Grid 7 M4 31.90 V/m	Grid 8 M4 45.38 V/m	Grid 9 M4 45.38 V/m

Cursor:

Total = 56.08 V/m

E Category: M4

Location: -8, -14, 8.7 mm



0 dB = 56.08 V/m = 34.98 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H110C-CDMA BC0-RC3 SO55-777CH

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 848.31 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1000 A/m; Power Drift = -0.10 dB

PMR not calibrated. PMF = 0.9900 is applied.

H-field emissions = 0.1581 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

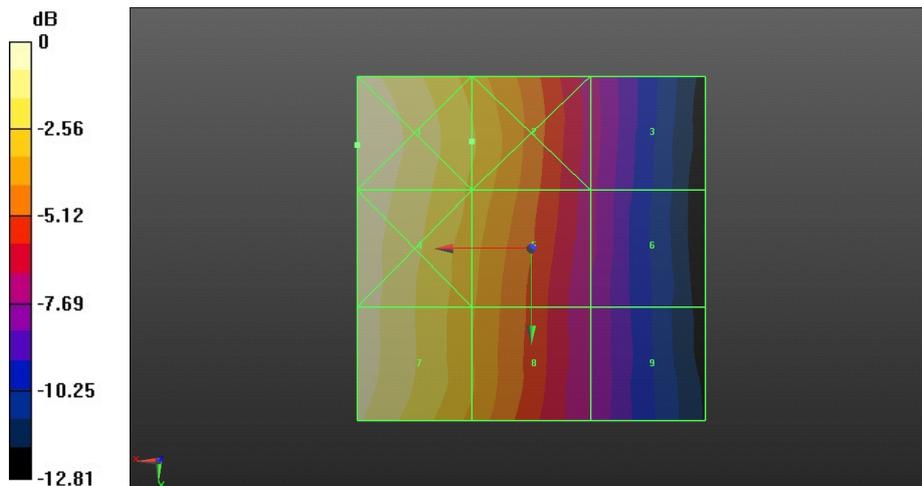
Grid 1 M4 0.166 A/m	Grid 2 M4 0.125 A/m	Grid 3 M4 0.073 A/m
Grid 4 M4 0.161 A/m	Grid 5 M4 0.121 A/m	Grid 6 M4 0.071 A/m
Grid 7 M4 0.158 A/m	Grid 8 M4 0.113 A/m	Grid 9 M4 0.069 A/m

Cursor:

Total = 0.1655 A/m

H Category: M4

Location: 25, -15, 8.7 mm



0 dB = 0.1655 A/m = -15.62 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H110C-CDMA BC0-RC3 SO55-384CH

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 836.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1020 A/m; Power Drift = -0.11 dB

PMR not calibrated. PMF = 0.9900 is applied.

H-field emissions = 0.1682 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

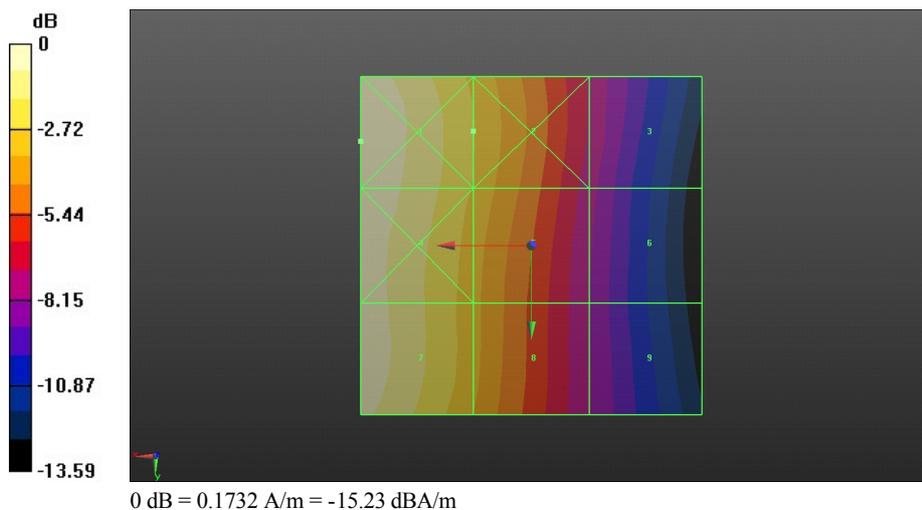
Grid 1 M4 0.173 A/m	Grid 2 M4 0.127 A/m	Grid 3 M4 0.075 A/m
Grid 4 M4 0.169 A/m	Grid 5 M4 0.125 A/m	Grid 6 M4 0.071 A/m
Grid 7 M4 0.168 A/m	Grid 8 M4 0.119 A/m	Grid 9 M4 0.069 A/m

Cursor:

Total = 0.1732 A/m

H Category: M4

Location: 25, -15.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H110C-CDMA BC0-RC3 SO55-1013CH

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 824.7 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09600 A/m; Power Drift = 0.03 dB

PMR not calibrated. PMF = 0.9900 is applied.

H-field emissions = 0.1628 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

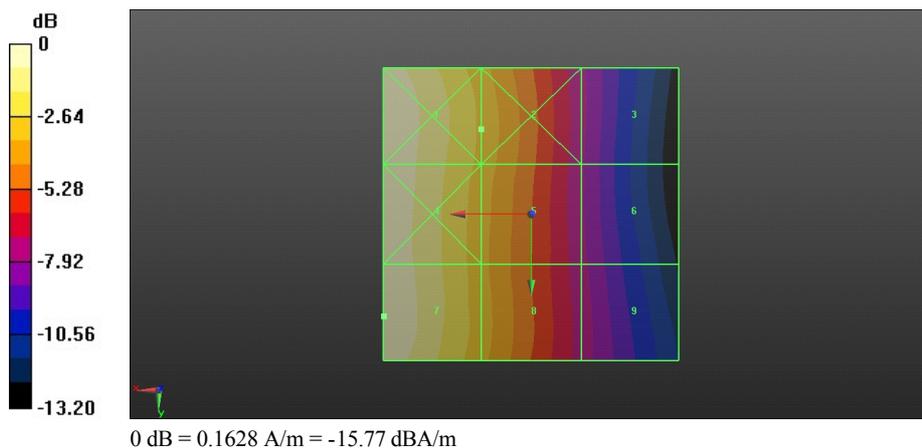
Grid 1 M4 0.162 A/m	Grid 2 M4 0.118 A/m	Grid 3 M4 0.068 A/m
Grid 4 M4 0.161 A/m	Grid 5 M4 0.116 A/m	Grid 6 M4 0.068 A/m
Grid 7 M4 0.163 A/m	Grid 8 M4 0.114 A/m	Grid 9 M4 0.070 A/m

Cursor:

Total = 0.1628 A/m

H Category: M4

Location: 25, 17.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H110C-CDMA BC0-RC3 SO55-384CH with battery 2#

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 836.52 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1030 A/m; Power Drift = 0.00 dB

PMR not calibrated. PMF = 0.9900 is applied.

H-field emissions = 0.1719 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

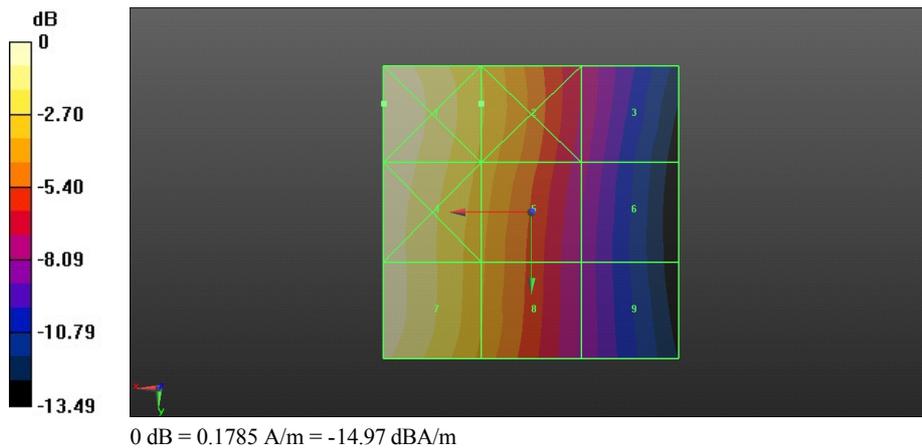
Grid 1 M4 0.179 A/m	Grid 2 M4 0.133 A/m	Grid 3 M4 0.078 A/m
Grid 4 M4 0.176 A/m	Grid 5 M4 0.128 A/m	Grid 6 M4 0.074 A/m
Grid 7 M4 0.172 A/m	Grid 8 M4 0.121 A/m	Grid 9 M4 0.070 A/m

Cursor:

Total = 0.1785 A/m

H Category: M4

Location: 25, -18.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H110C-CDMA BC1-RC3 SO55-1175CH

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1908.75 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1070 A/m; Power Drift = -0.13 dB

PMR not calibrated. PMF = 0.9400 is applied.

H-field emissions = 0.1193 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

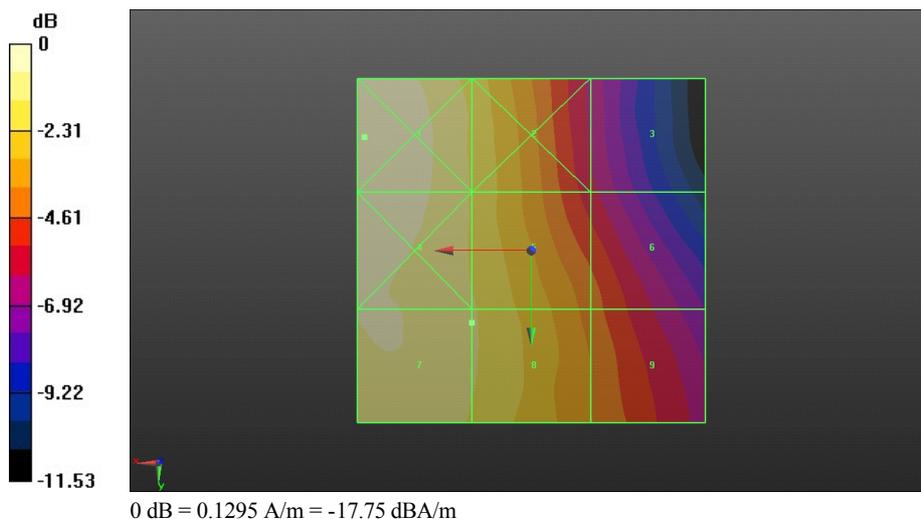
Grid 1 M4 0.130 A/m	Grid 2 M4 0.108 A/m	Grid 3 M4 0.066 A/m
Grid 4 M4 0.127 A/m	Grid 5 M4 0.110 A/m	Grid 6 M4 0.080 A/m
Grid 7 M4 0.119 A/m	Grid 8 M4 0.110 A/m	Grid 9 M4 0.084 A/m

Cursor:

Total = 0.1295 A/m

H Category: M4

Location: 24, -16.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H110C-CDMA BC1-RC3 SO55-600CH

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1150 A/m; Power Drift = 0.02 dB

PMR not calibrated. PMF = 0.9400 is applied.

H-field emissions = 0.1175 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

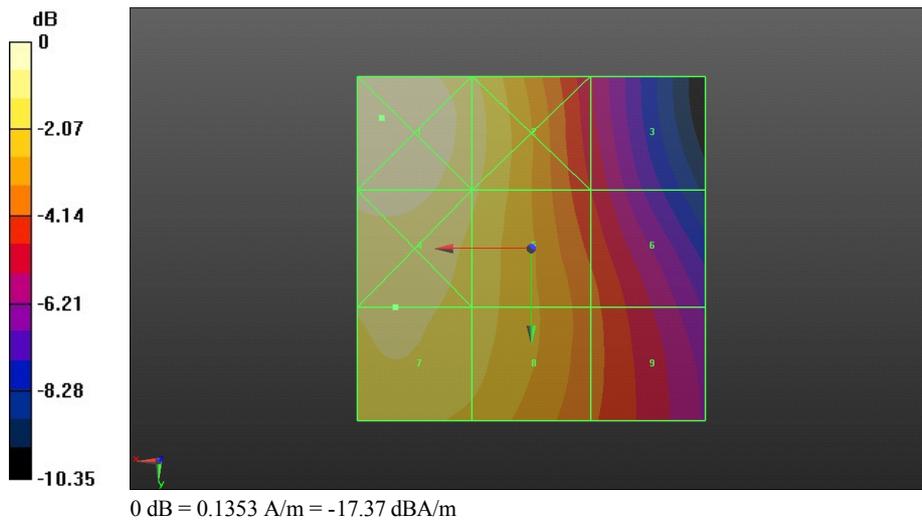
Grid 1 M4 0.135 A/m	Grid 2 M4 0.120 A/m	Grid 3 M4 0.078 A/m
Grid 4 M4 0.128 A/m	Grid 5 M4 0.117 A/m	Grid 6 M4 0.087 A/m
Grid 7 M4 0.118 A/m	Grid 8 M4 0.111 A/m	Grid 9 M4 0.087 A/m

Cursor:

Total = 0.1353 A/m

H Category: M4

Location: 21.5, -19, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H110C-CDMA BC1-RC3 SO55-25CH

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1851.25 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1370 A/m; Power Drift = 0.06 dB

PMR not calibrated. PMF = 0.9400 is applied.

H-field emissions = 0.1425 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

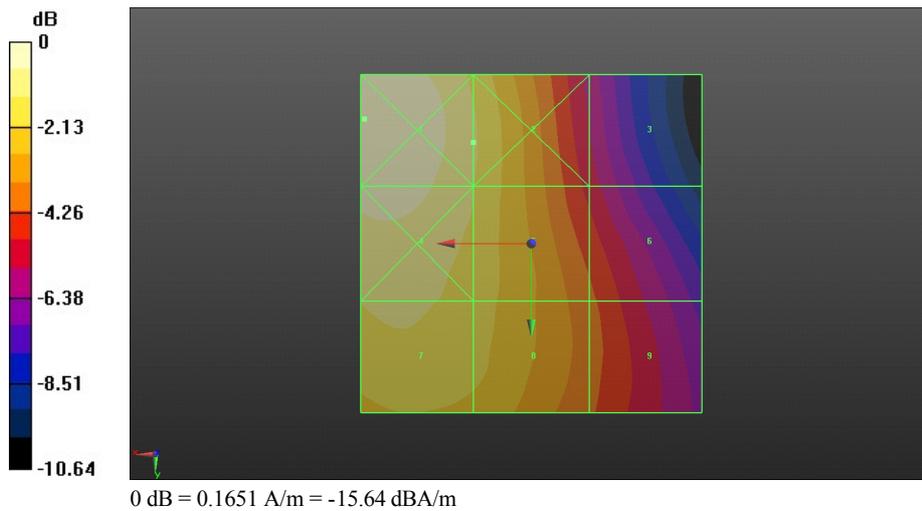
Grid 1 M4 0.165 A/m	Grid 2 M4 0.142 A/m	Grid 3 M4 0.091 A/m
Grid 4 M4 0.158 A/m	Grid 5 M4 0.141 A/m	Grid 6 M4 0.104 A/m
Grid 7 M4 0.143 A/m	Grid 8 M4 0.135 A/m	Grid 9 M4 0.105 A/m

Cursor:

Total = 0.1651 A/m

H Category: M4

Location: 24.5, -18.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H110C-CDMA BC1-RC3 SO55-25CH with battery 2#

DUT: H110C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1851.25 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn1305; Calibrated: 2013-1-8
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1380 A/m; Power Drift = 0.00 dB

PMR not calibrated. PMF = 0.9400 is applied.

H-field emissions = 0.1431 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

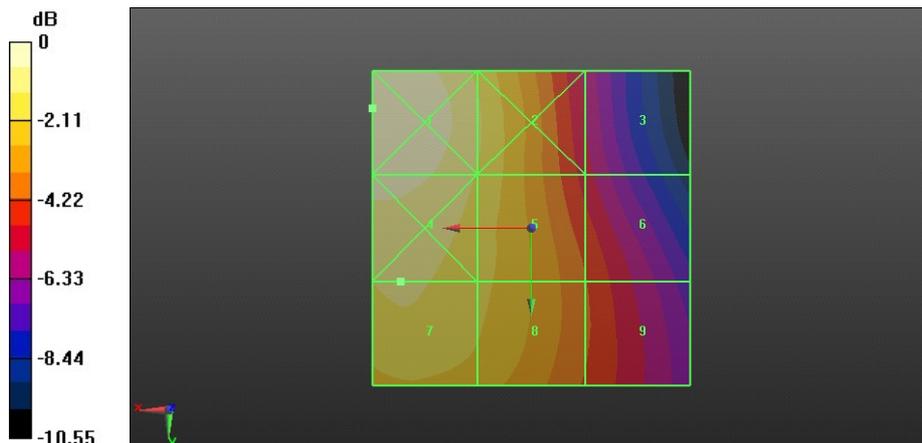
Grid 1 M4 0.166 A/m	Grid 2 M4 0.143 A/m	Grid 3 M4 0.091 A/m
Grid 4 M4 0.158 A/m	Grid 5 M4 0.141 A/m	Grid 6 M4 0.103 A/m
Grid 7 M4 0.143 A/m	Grid 8 M4 0.134 A/m	Grid 9 M4 0.104 A/m

Cursor:

Total = 0.1660 A/m

H Category: M4

Location: 25, -19, 8.7 mm



0 dB = 0.1660 A/m = -15.60 dBA/m